

INFORMATION DISCLOSURE STATEMENT

Applicant	: Todd et al.
App. No.	: Unknown
Filed	: Herewith
For	: METHOD TO FORM ULTRA HIGH QUALITY SILICON-CONTAINING COMPOUND LAYERS
Examiner	: Unknown
Group Art Unit	: Unknown

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing six (6) references that are also enclosed.

This Information Disclosure Statement is being filed within three months of the filing date of this application or upon filing if this is a CPA or RCE, and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: July 18, 2003

By: Adeel Syed Akhtar

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMEX.376A	APPLICATION NO. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Todd et al.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
1	4,851,095	7/25/89	Scobey et al.			
2	5,916,365	6/29/99	Sherman			
3	6,015,590	1/18/00	Suntola et al.			
4	6,159,828	12/12/00	Ping et al.			
5	6,200,893 B1	3/13/01	Sneh			

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
6	Iyer, R. Suryanarayanan et al., "A process Method of Silicon Nitride Atomic Layer Cyclic Deposition," Semicon Taiwan 2001, pp. 17-25
7	
8	
9	
10	

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EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED. WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 600; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	